

SOT-323 Plastic-Encapsulated Transistors

2SB1218A TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 150 \text{ mW (Tamb=25°C)}$$

Collector current

$$I_{CM}: -100 \text{ mA}$$

Collector-base voltage

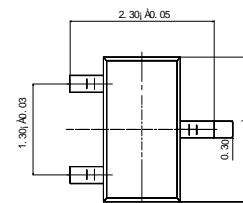
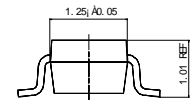
$$V_{(BR)CBO}: -45 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-45			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2mA, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -2mA$	160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.5	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA, f = 200MHz$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.7		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	160-260	210-340	290-460
Marking	BQ	BR	BS